

20 V, single P-channel Trench MOSFET 12 February 2013

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Low on-state resistance
- Trench MOSFET technology

3. Applications

- Low power DC-to-DC converters
- Load switching
- Battery management
- Battery powered portable equipment

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage	_		-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C		-	-	-4.3	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -2.8 A; T _j = 25 °C		-	58	74	mΩ





20 V, single P-channel Trench MOSFET

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain		G
			TO-236AB (SOT23)	S 017aaa257

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMV65XP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV65XP	%M9

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

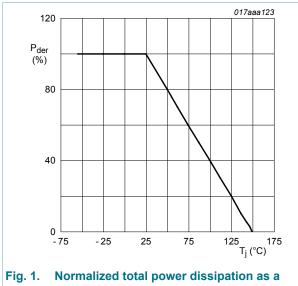
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C		-	-4.3	А
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-2.8	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.8	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-16	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	480	mW
			[1]	-	833	mW
		T _{sp} = 25 °C		-	4165	mW

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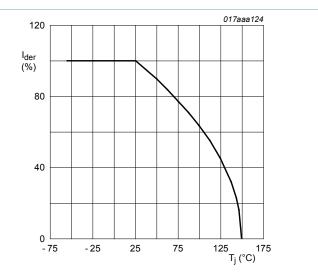
20 V, single P-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit	
Tj	junction temperature			-55	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain diode							
I _S	source current	T _{sp} = 25 °C		-	-1.6	А	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm². [2]
 - Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



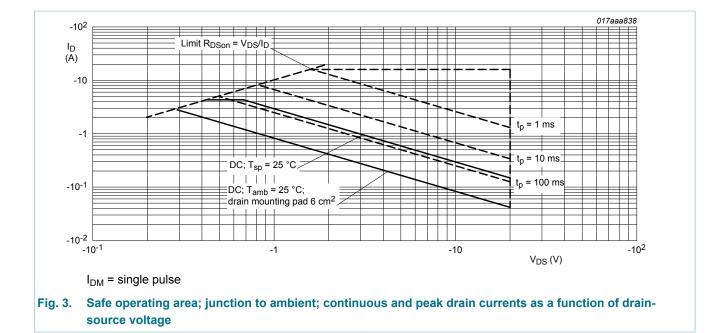
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$





$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

20 V, single P-channel Trench MOSFET



9. Thermal characteristics

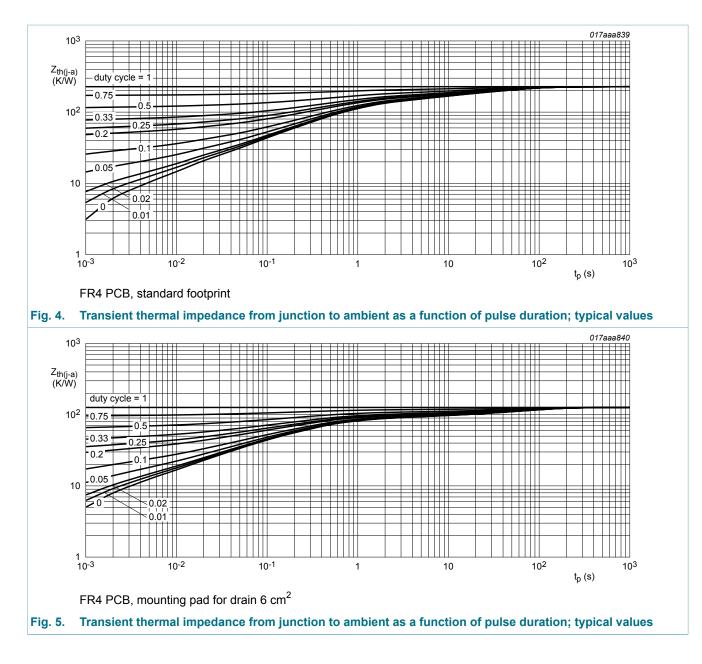
Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from ju	thermal resistance		[1]	-	230	260	K/W
	from junction to ambient		[2]	-	125	150	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

20 V, single P-channel Trench MOSFET

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10. Characteristics

Table 7. C	haracteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C		-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C		-0.47	-0.65	-0.9	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C		-	-	-100	μA
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Product data sheet

PMV65XP

20 V, single P-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -2.8 A; T _j = 25 °C	-	58	74	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2.8 A; T _j = 150 °C	-	82	105	mΩ
		V_{GS} = -2.5 V; I _D = -2.3 A; T _j = 25 °C	-	67	92	mΩ
		V _{GS} = -1.8 V; I _D = -1 A; T _j = 25 °C	-	87	135	mΩ
9fs	forward transconductance	V _{DS} = -10 V; I _D = -2.8 A; T _j = 25 °C	-	15	-	S
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -6 V; I_D = -2.8 A; V_{GS} = -4.5 V; T_j = 25 °C	-	7.7	-	nC
Q _{GS}	gate-source charge		-	1	-	nC
Q _{GD}	gate-drain charge		-	1.65	-	nC
C _{iss}	input capacitance	V _{DS} = -20 V; f = 1 MHz; V _{GS} = 0 V;	-	744	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	65	-	pF
C _{rss}	reverse transfer capacitance		-	53	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -6 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ;	-	7	-	ns
t _r	rise time	T _j = 25 °C; I _D = -1 A	-	18	-	ns
t _{d(off)}	turn-off delay time		-	135	-	ns
t _f	fall time	1	-	68	-	ns

Source-drain diode

source-drain voltage

 V_{SD}

I_S = -0.9 A; V_{GS} = 0 V; T_j = 25 °C

-1.2

V

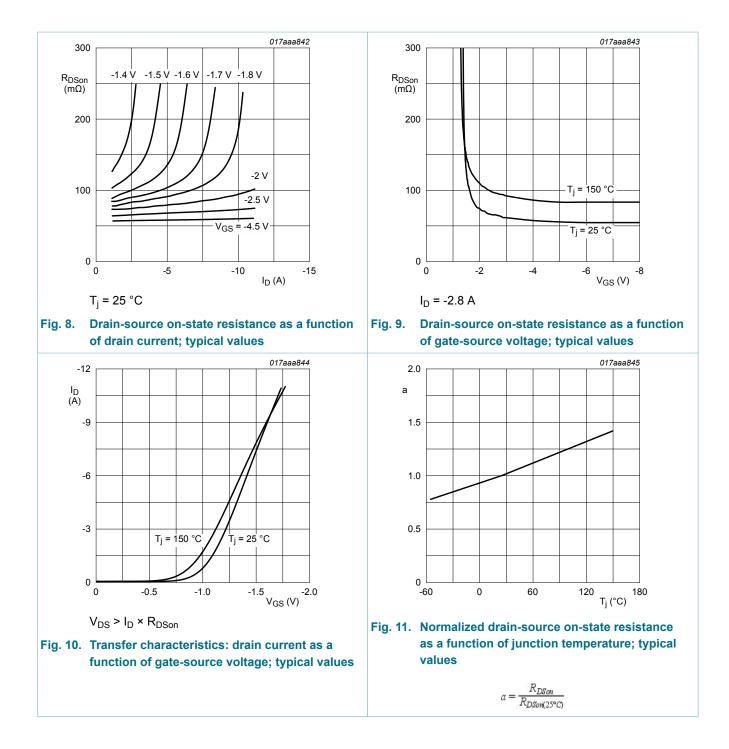
-0.8

-

017aaa841 017aaa850 10⁻³ -12 -4.5 V V_{GS} = -1.8 V I_D (A) .-2.5 V I_D (A) v -1.7 V -9 10⁻⁴ 1.6 V min max typ -6 . -1.5 V 10⁻⁵ -3 -1.3 V 10⁻⁶ 0 -3.75 V_{DS} (V) 0.8 1.0 V_{GS} (V) -1.25 -2.50 0 0.2 0.4 0.6 0 -5.00 T_i = 25 °C T_j = 25 °C; V_{DS} = -5 V Output characteristics: drain current as a Fig. 7. Sub-threshold drain current as a function of Fig. 6. function of drain-source voltage; typical values gate-source voltage PMV65XP All information provided in this document is subject to legal disclaimers. © NXP B.V. 2013. All rights reserved

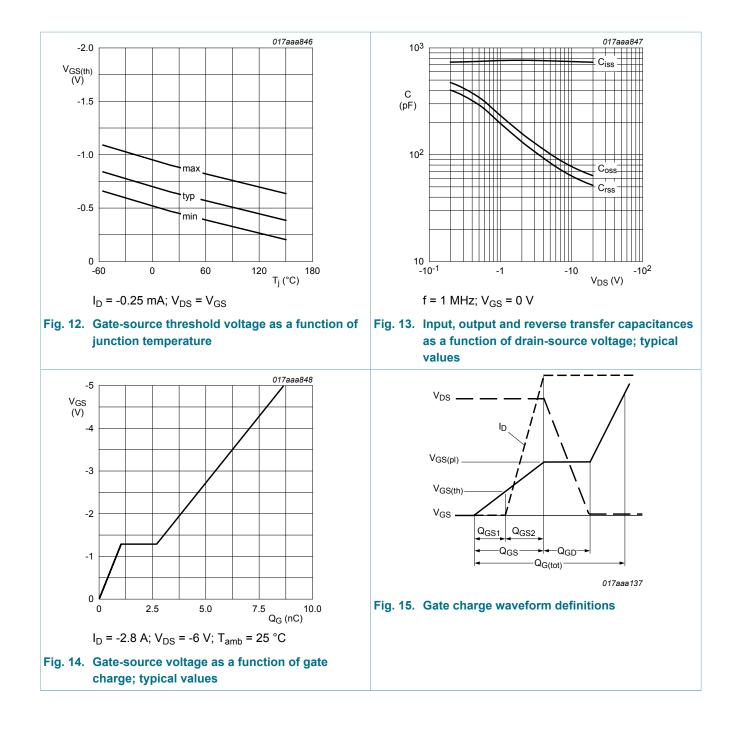
Product data sheet

20 V, single P-channel Trench MOSFET



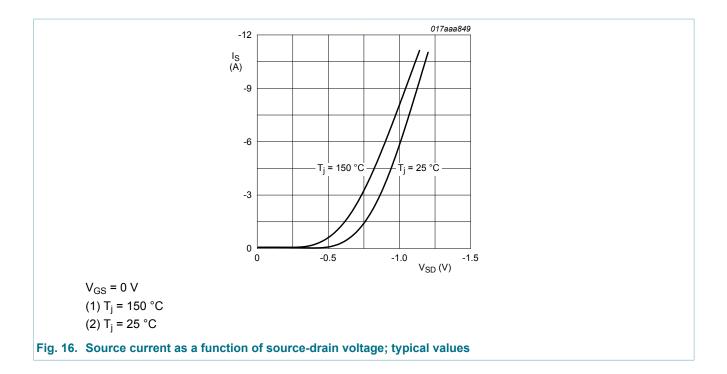
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20 V, single P-channel Trench MOSFET

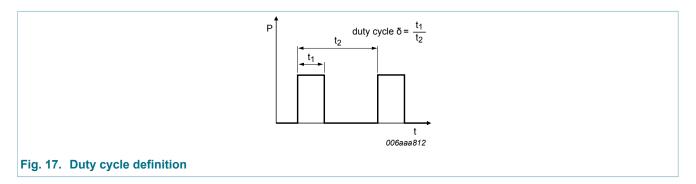


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20 V, single P-channel Trench MOSFET

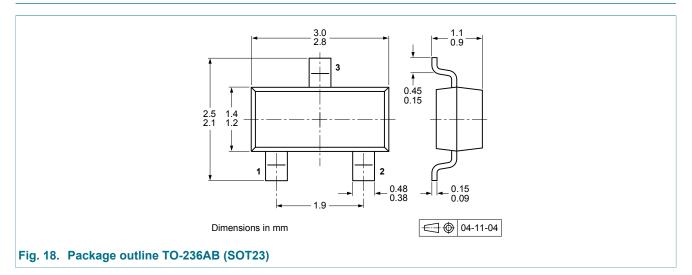


11. Test information

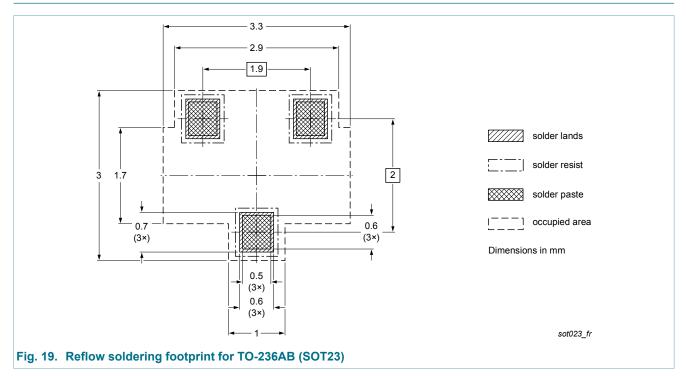


20 V, single P-channel Trench MOSFET

12. Package outline

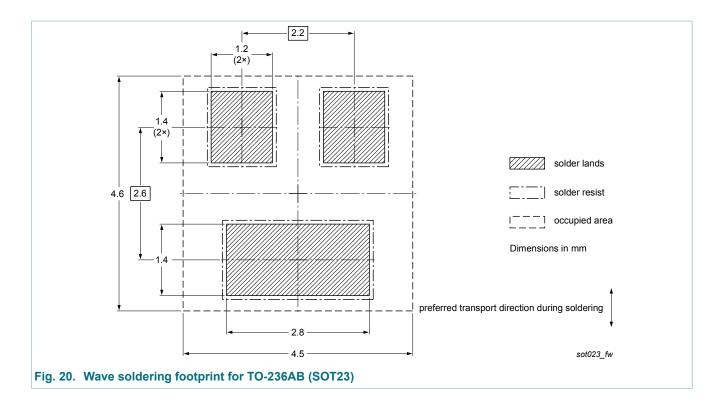


13. Soldering



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14. Revision history

Table 8.Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV65XP v.2	20130212	Product data sheet	-	PMV65XP v.1
Modifications:	Pinning information	corrected		
PMV65XP v.1	20120921	Product data sheet	-	-

20 V, single P-channel Trench MOSFET

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15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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20 V, single P-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	9
12	Package outline	10
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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